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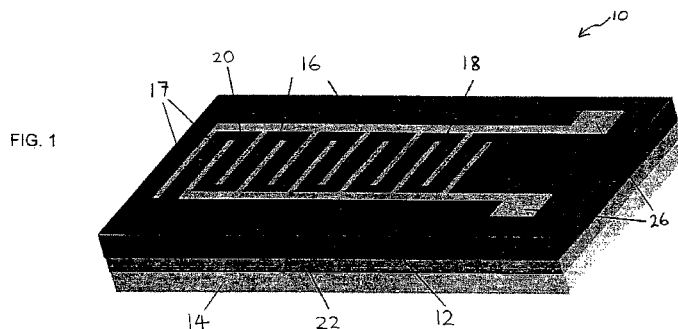
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(54) Title: A PIEZOELECTRIC SENSOR AND A METHOD OF FABRICATING A PIEZOELECTRIC SENSOR



(57) Abstract: A piezoelectric sensor comprising a piezoelectric film formed on a surface of an object to be monitored; a plurality of electrodes formed on a surface of the piezoelectric film; and wherein electrical polarization of the piezoelectric film is about coplanar with the surface of the piezoelectric film. A method of forming a piezoelectric sensor. The method comprises forming a piezoelectric film on a surface of an object to be monitored; forming electrodes on a surface of the piezoelectric film; and orientating electrical polarization in the piezoelectric film to be about coplanar with the surface of the piezoelectric film.